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## (54) HIGH ELECTRON MOBILITY TRANSISTOR AND METHOD FOR FABRICATING THE

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#### (57) ABSTRACT

A high electron mobility transistor (HEMT) includes a buffer layer on a substrate, a barrier layer on the buffer layer, a p-type semiconductor layer on the barrier layer, a first layer adjacent to a first side of the p-type semiconductor layer without extending to a second side of the p-type semiconductor layer, and a second layer adjacent to the second side of the p-type semiconductor layer without extending to the first side of the p-type semiconductor layer.

